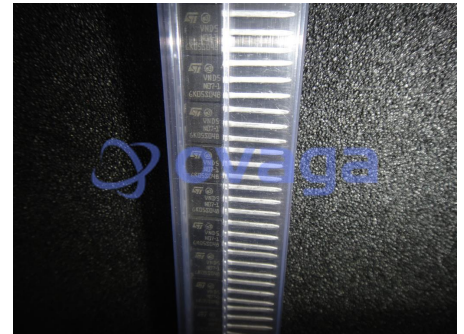


OMNIFET FULLY AUTOPROTECTED POWER MOSFET, MOSFET OMNIFET III
FULLY AUTO PROTECT Pwr MOSFET

Manufacturers	STMicroelectronics, Inc
Package/Case	IPAK-3
Product Type	Power Management ICs
RoHS	Rohs
Lifecycle	



Images are for reference only

Please submit RFQ for VND5N07-1-E or [Email to us: sales@ovaga.com](mailto:sales@ovaga.com) We will contact you in 12 hours.

[RFQ](#)

General Description

VND5N07-1-E is a type of power MOSFET transistor produced by STMicroelectronics. Here are some of its features:

Features

Drain-source voltage (V_{dss}): 70V

Continuous drain current (I_d): 5A

On-state resistance (R_{ds(on)}): 0.38Ω

Maximum junction temperature (T_j): 150°C

Operating temperature range (T_j): -55°C to 150°C

Application

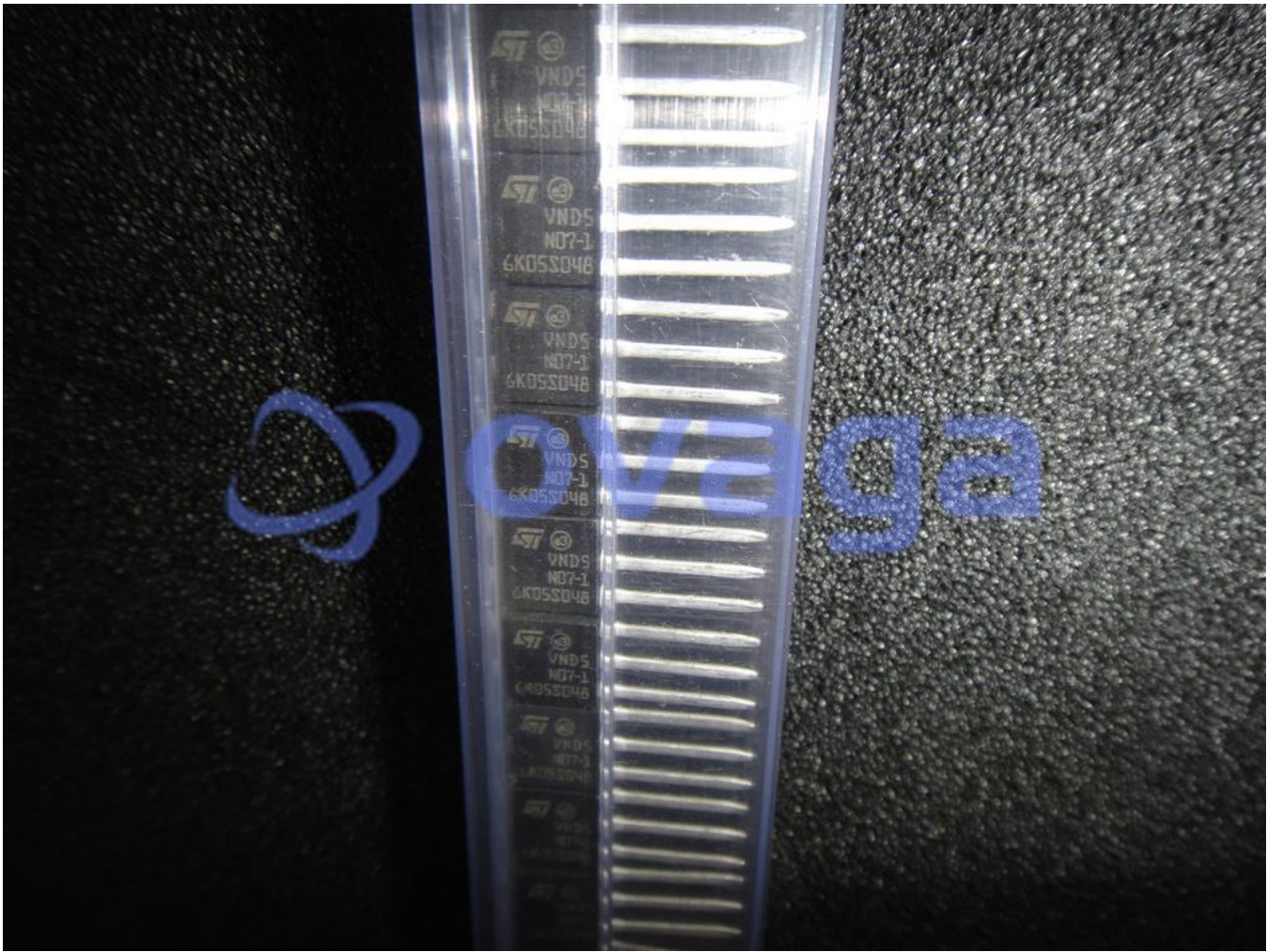
DC-DC converters

Motor control circuits

Lighting systems

Switching power supplies

Audio amplifiers



Related Products



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STMicroelectronics, Inc
TO-252



[VNB35NV04](#)

STMicroelectronics, Inc
D2PAK



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[VND5N07-E](#)

STMicroelectronics, Inc
TO-252